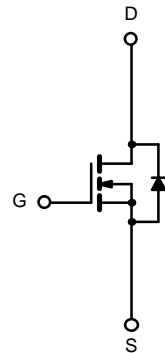
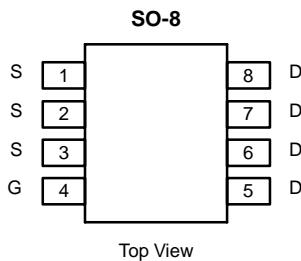




## N-Channel 80-V (D-S) MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
80	0.0165 @ $V_{GS} = 10$ V	9.5
	0.022 @ $V_{GS} = 6.0$ V	8.3

**TrenchFET<sup>®</sup>**  
Power MOSFETs



Ordering Information: Si4896DY  
Si4896DY-T1 (with Tape and Reel)

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		$V_{DS}$	80		V
Gate-Source Voltage		$V_{GS}$	$\pm 20$		
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>a</sup>	$T_A = 25^\circ\text{C}$	$I_D$	9.5	6.7	A
	$T_A = 70^\circ\text{C}$		7.6	5.4	
Pulsed Drain Current		$I_{DM}$	50		
Avalanch Current		$I_{AS}$	40		
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	2.8	1.4	
Maximum Power Dissipation <sup>a</sup>	$T_A = 25^\circ\text{C}$	$P_D$	3.1	1.56	W
	$T_A = 70^\circ\text{C}$		2.0	1.0	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 150		$^\circ\text{C}$

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10$ sec	$R_{thJA}$	33	40	$^\circ\text{C/W}$
	Steady State		65	80	
Maximum Junction-to-Foot (Drain)		$R_{thJF}$	17	21	

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

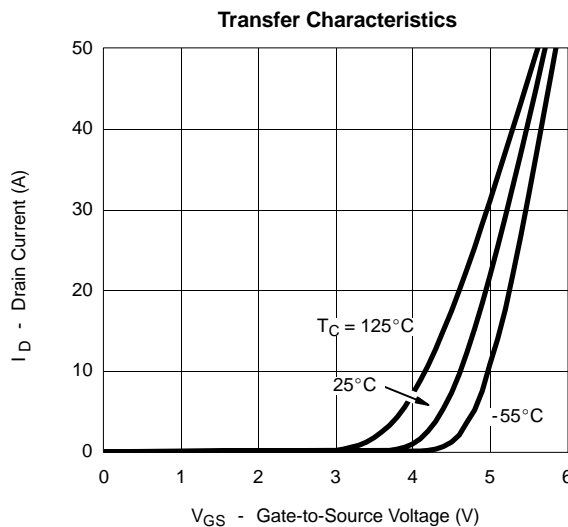
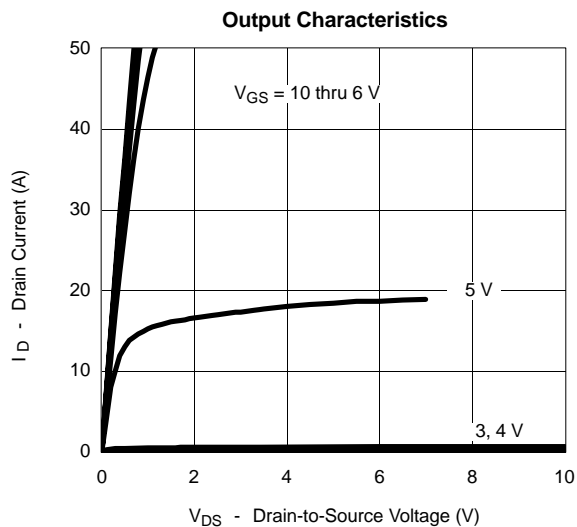
**SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.0			V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 64 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 64 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			5	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	50			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A		0.0135	0.0165	Ω
		V <sub>GS</sub> = 6.0 V, I <sub>D</sub> = 8.0 A		0.0175	0.022	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		25		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 2.8 A, V <sub>GS</sub> = 0 V		0.75	1.1	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A		34	41	nC
Gate-Source Charge	Q <sub>gs</sub>			7.5		
Gate-Drain Charge	Q <sub>gd</sub>			11.0		
Gate Resistance	R <sub>g</sub>		0.2	0.85	1.2	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 40 V, R <sub>L</sub> = 40 Ω I <sub>D</sub> ≅ 1.0 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 6 Ω		17	25	ns
Rise Time	t <sub>r</sub>			11	17	
Turn-Off Delay Time	t <sub>d(off)</sub>			40	60	
Fall Time	t <sub>f</sub>			31	45	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>		I <sub>F</sub> = 2.8 A, di/dt = 100 A/μs		45	

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

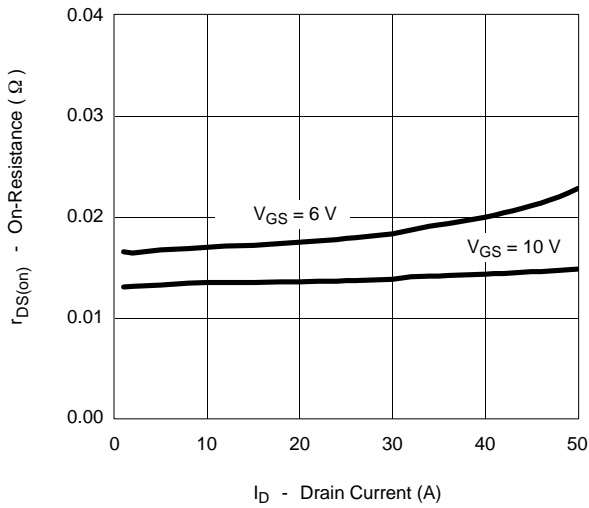
**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**



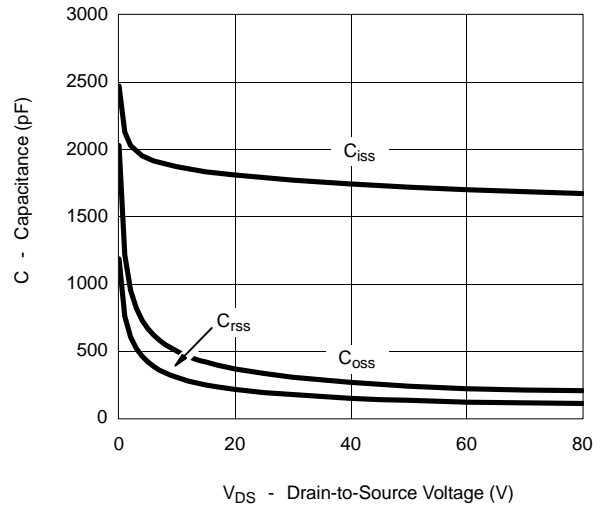


**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

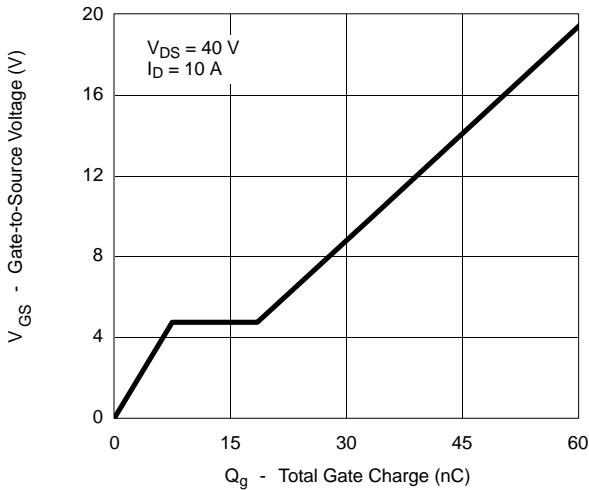
**On-Resistance vs. Drain Current**



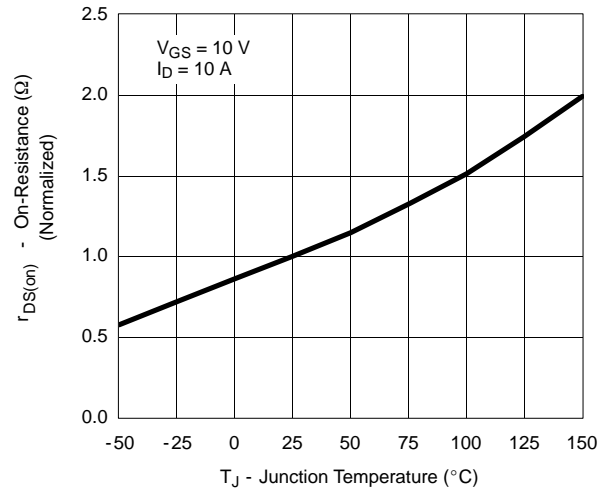
**Capacitance**



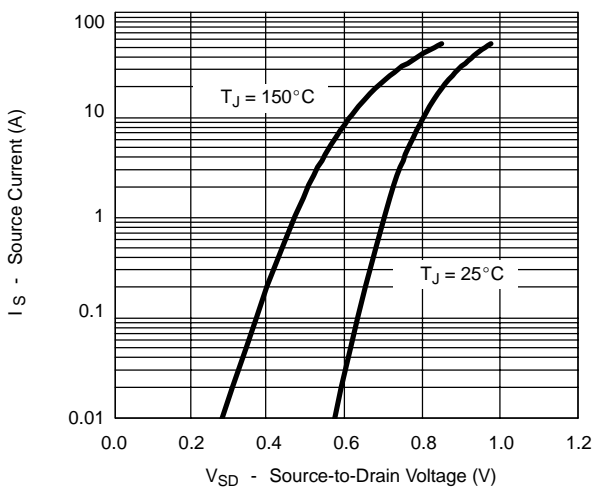
**Gate Charge**



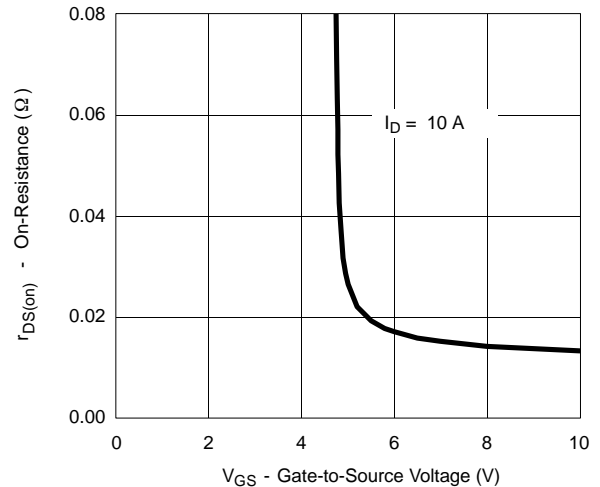
**On-Resistance vs. Junction Temperature**



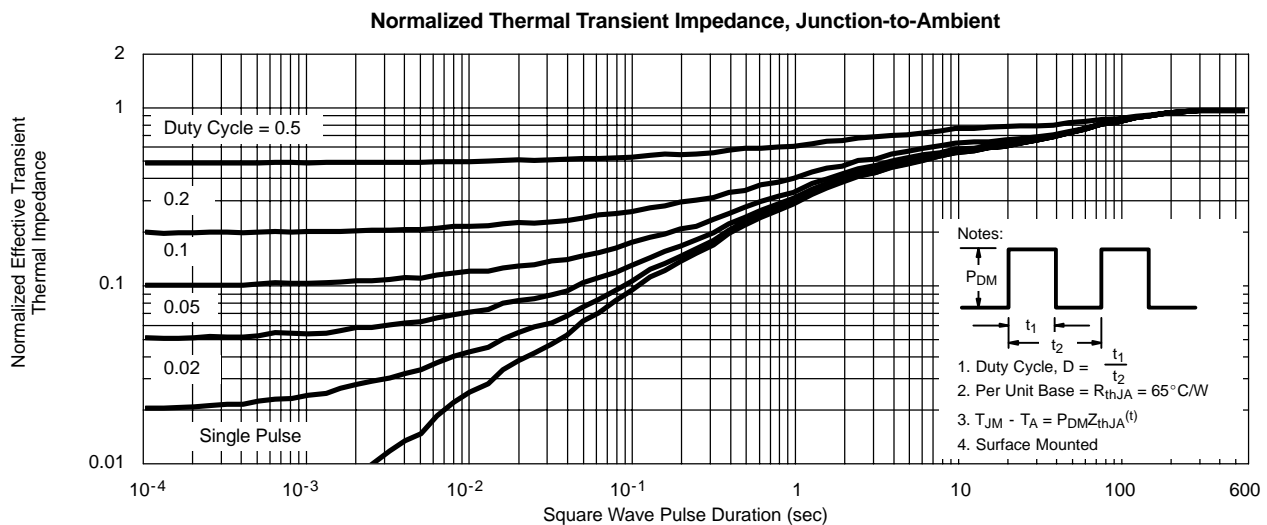
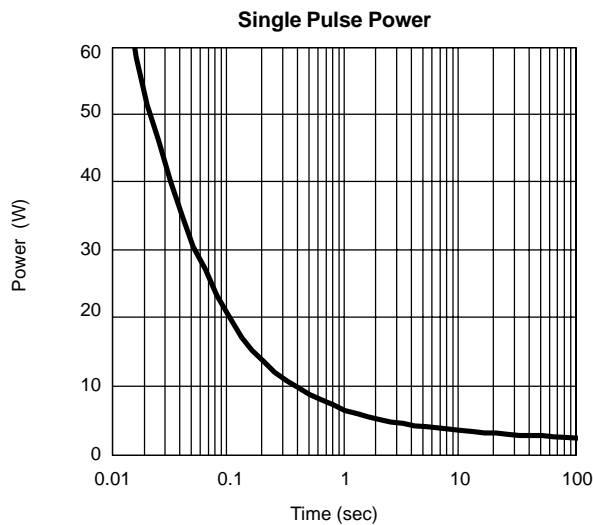
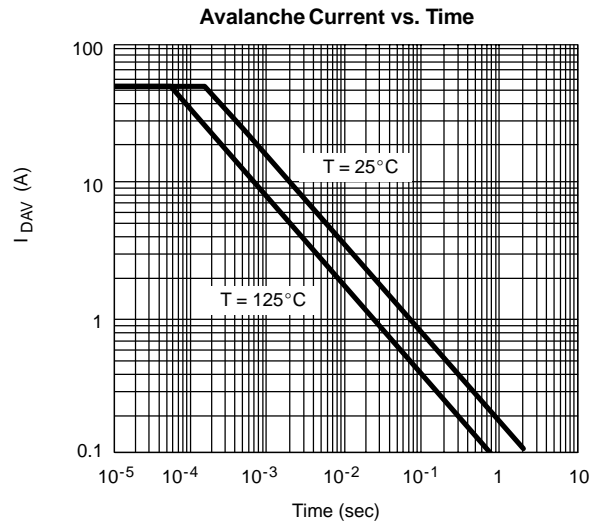
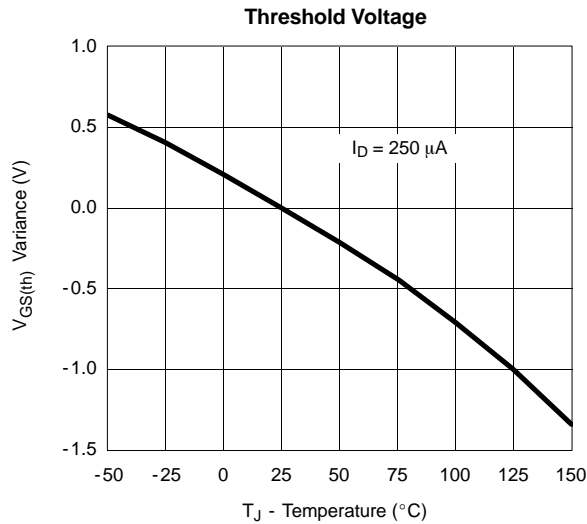
**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**

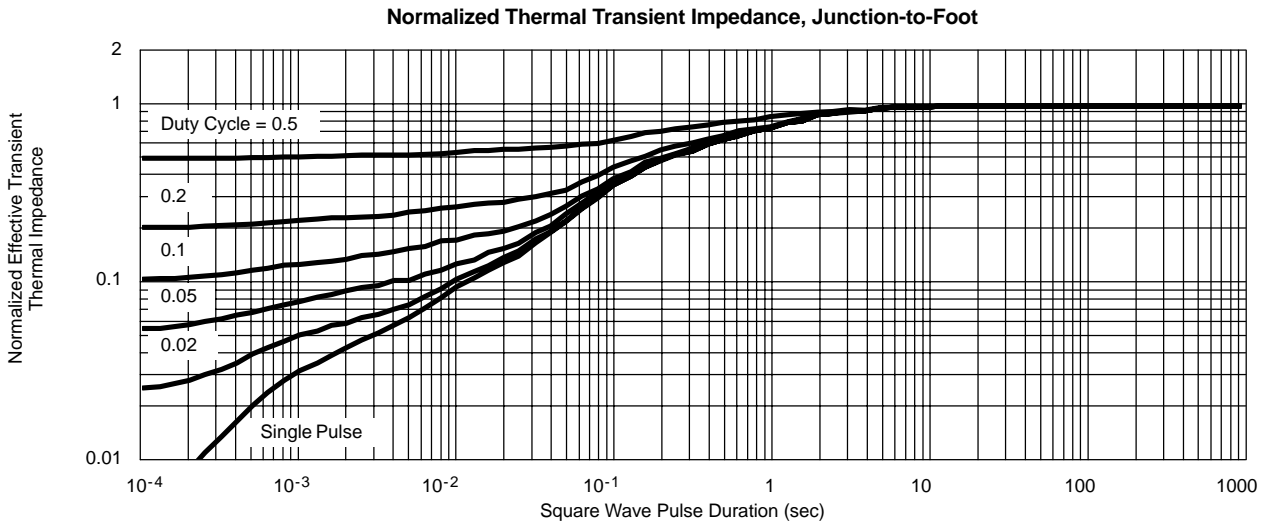


**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**





**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**





## Notice

Specifications of the products displayed herein are subject to change without notice. Vishay Intertechnology, Inc., or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document. Except as provided in Vishay's terms and conditions of sale for such products, Vishay assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of Vishay products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Vishay for any damages resulting from such improper use or sale.